



## DMPH4023SK3Q

#### 40V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
-40V	26mΩ @ $V_{GS}$ = -10V	-50A

#### **Features**

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

# **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

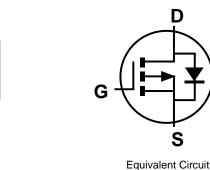
- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment



Top View

# **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish—Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



### Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH4023SK3Q-13	TO252 (DPAK)	2500/Tape & Reel

D

U D

Pin Out

Top View

S

G

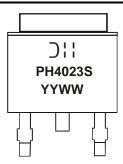
Notes:

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, see https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



) | | = Manufacturer's Marking PH4023S = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-40	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 7) $V_{GS}$ = -10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	Ι <sub>D</sub>	-50 -35	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	-70	A
Maximum Continuous Body Diode Forward Current (Note 7)		Is	-4	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	-70	A
Avalanche Current, L = 0.1mH (Note 8)		IAS	-40	A
Avalanche Energy, L = 0.1mH (Note 8)		E <sub>AS</sub>	85	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 6)		PD	2.1	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>OJA</sub>	71	°C/W	
Total Power Dissipation (Note 7)		PD	3.6	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	R <sub>0JA</sub>	41	°C/W	
Thermal Resistance, Junction to Case		R <sub>eJC</sub>	1.5	C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

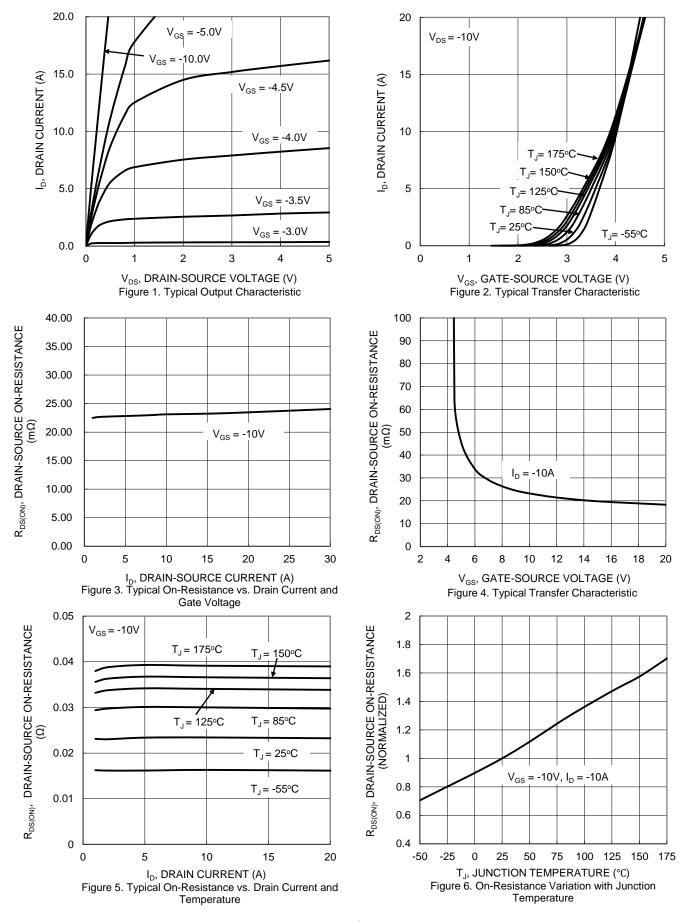
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Symbol		тур	IVIAX	Unit	Test condition	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40		_	V	$V_{GS} = 0V, I_{D} = -250 \mu A$	
Zero Gate Voltage Drain Current	IDSS			-1	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)				•		·	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	_	-3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	21	26	mΩ	$V_{GS} = -10V, I_D = -10A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	1091	_	рF		
Output Capacitance	Coss		288	—	pF	− V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V, − f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		111	_	pF		
Gate Resistance	Rg	_	14	—	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge	Qg	—	18.7	_	nC	V <sub>DS</sub> = -20V, I <sub>D</sub> = -10A,	
Gate-Source Charge	Q <sub>gs</sub>	_	4.2	—	nC	50 / 5 /	
Gate-Drain Charge	Q <sub>gd</sub>	_	5.0	—	nC	V <sub>GS</sub> = -10V	
Turn-On Delay Time	t <sub>D(ON)</sub>		5.3	_	ns		
Turn-On Rise Time	t <sub>R</sub>		4.8	—	ns	V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		30.7	—	ns	$R_G = 6\Omega$ , $I_D = -10A$	
Turn-Off Fall Time	t <sub>F</sub>		23.4	_	ns		
Reverse Recovery Time	t <sub>RR</sub>		17.8	_	ns		
Reverse Recovery Charge	Q <sub>RR</sub>		9.2	_	nC	I <sub>F</sub> = -10A, di/dt = -100A/μs	

6. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout. Notes:

7. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.

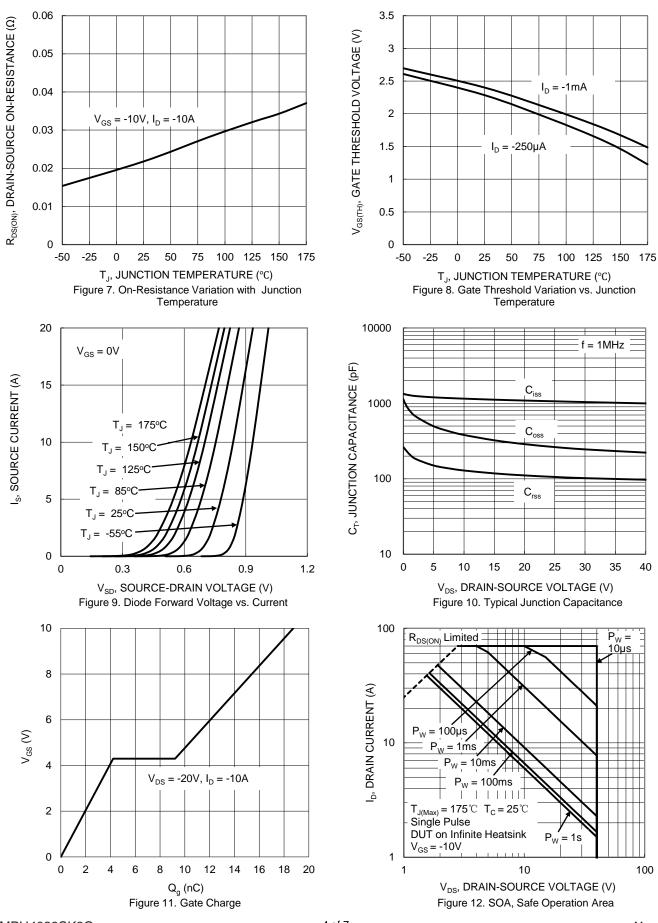
8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}$ C. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.



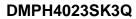


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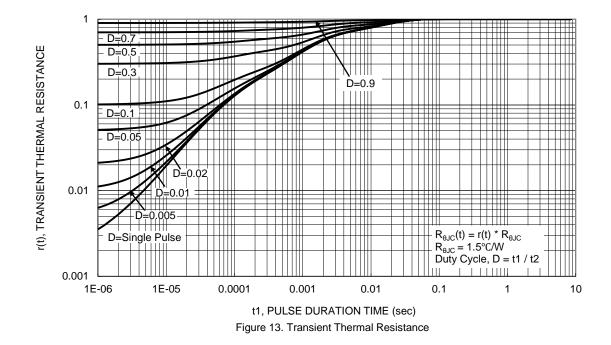




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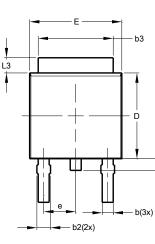


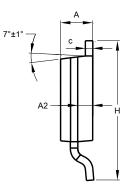


# **Package Outline Dimensions**

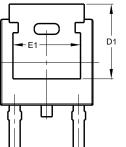
Please see http://www.diodes.com/package-outlines.html for the latest version.

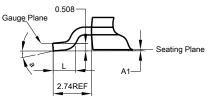
L4





TO252 (DPAK)

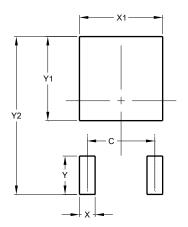




TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
c	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Ε	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
∟	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



TO252 (DPAK)

Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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